

Fig. 1A

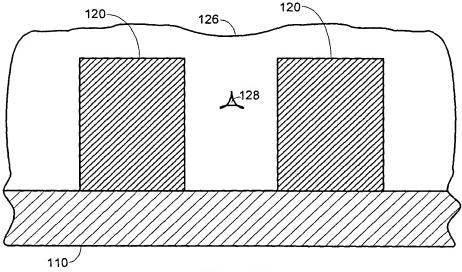


Fig. 1B

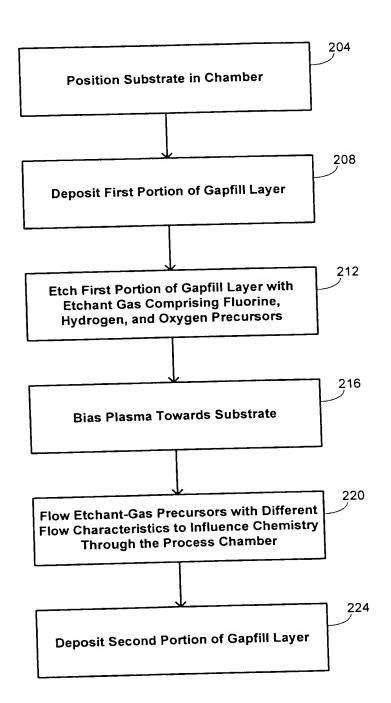


Fig. 2A

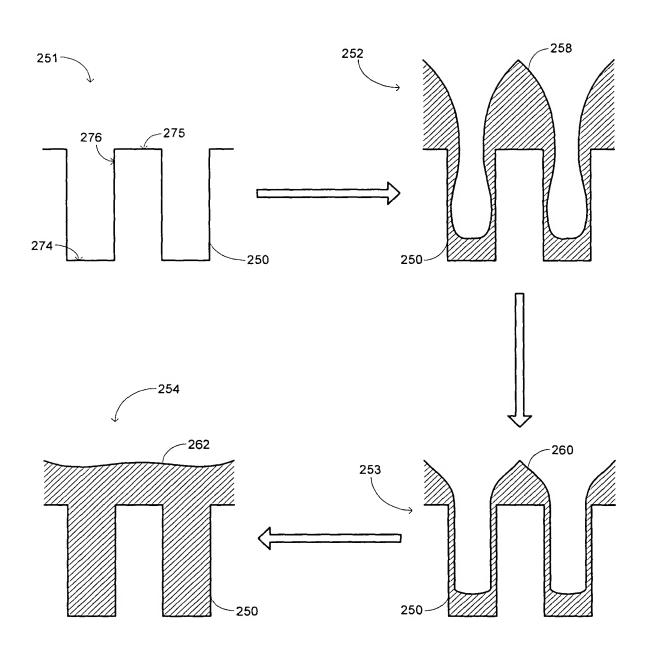
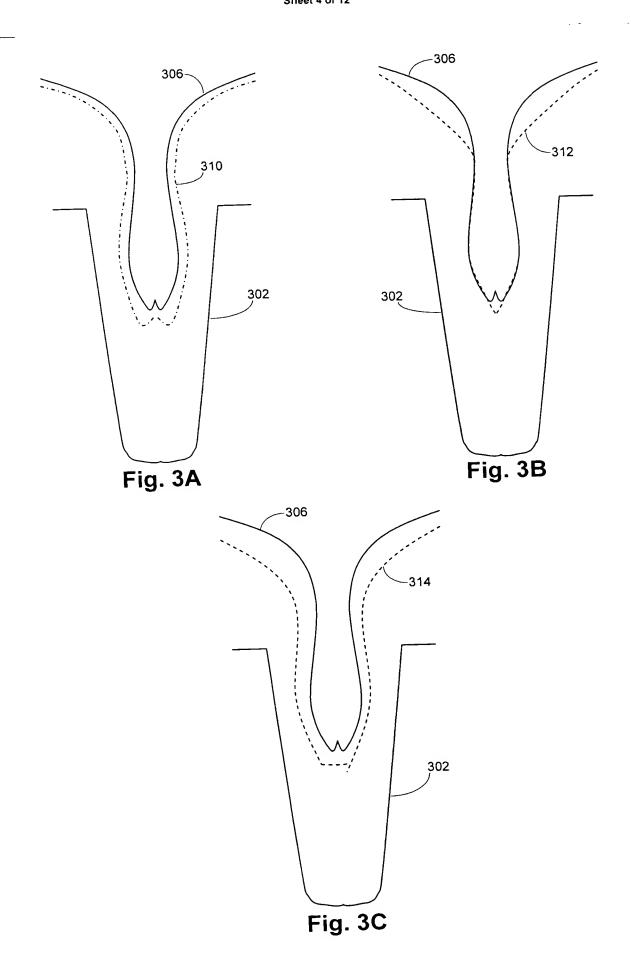
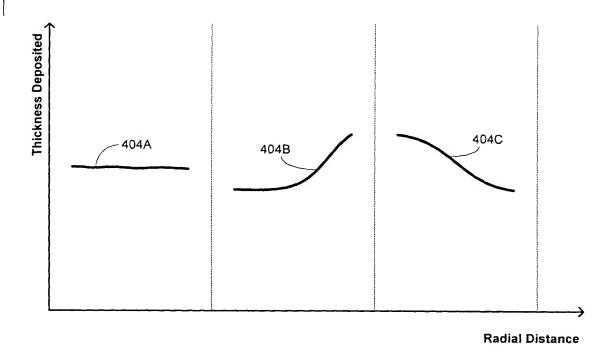


Fig. 2B

Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 4 of 12



Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 5 of 12



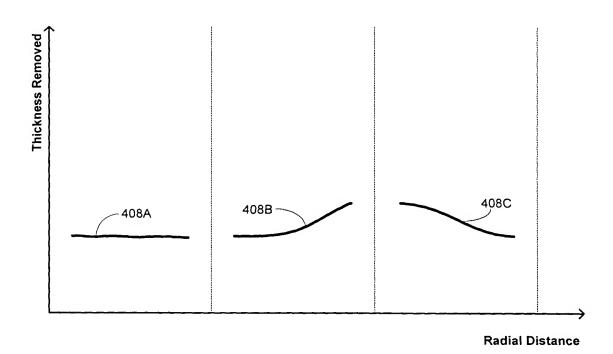
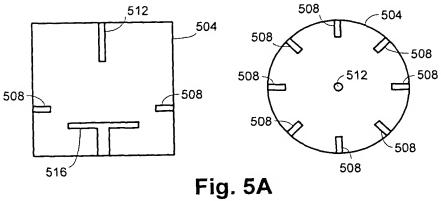
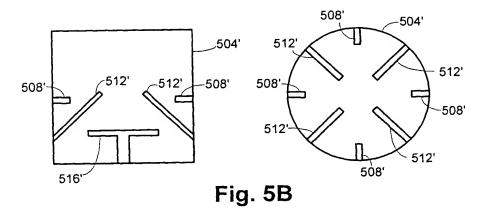
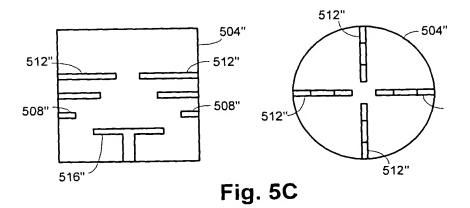


Fig. 4

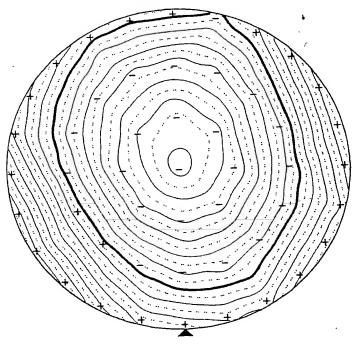






## Atty. Docket No.: A8067/T51700 Applicant: Hemant P. Mungekar et al. Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE FEATURE TOPOGRAPHY MODIFICATION Sheet 7 of 12

## NANOMETRICS 2D CONTOUR MAP



Wafer Size: 200mm Edge Exclusion: 3.0mm Points: 49 out of 49

Statistics Data:

 Mean:
 613Å

 StdD:
 154.4Å

 ZStdD:
 25.17Z

 ZNonU:
 47.02Z

 Max:
 898Å

 Min:
 321Å

 Range:
 577Å

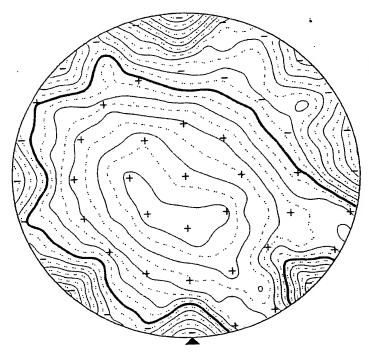
 Interval:
 23.1Å

 Zintervol:
 3.762Z

Comment:

Fig. 5D

## NANOMETRICS 2D CONTOUR MAP



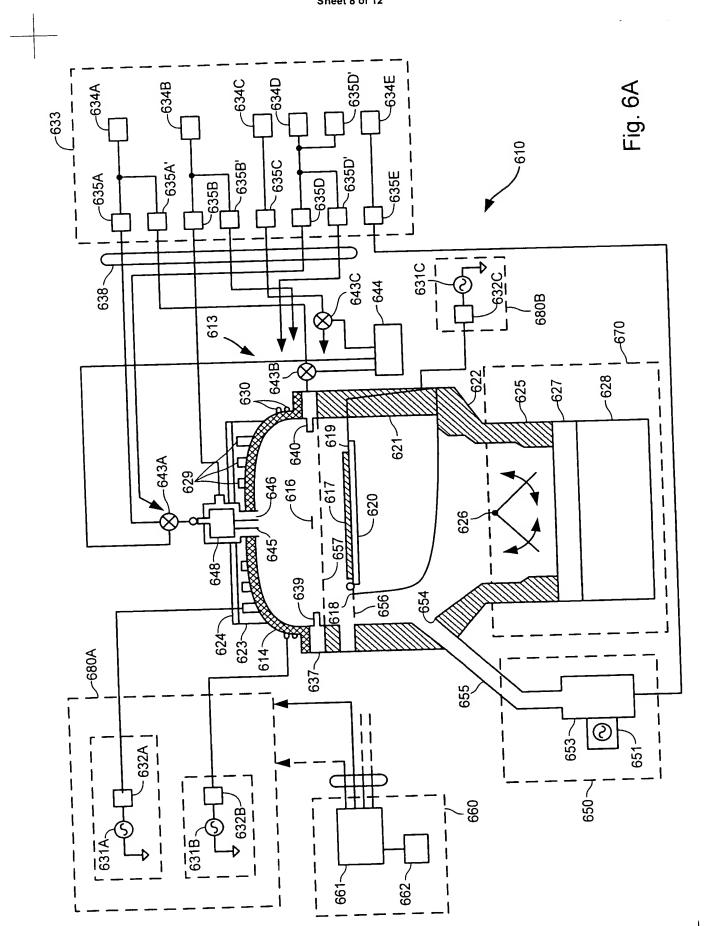
Wafer Size: 200mm Edge Exclusion: 3.0mm Points: 49 out of 49

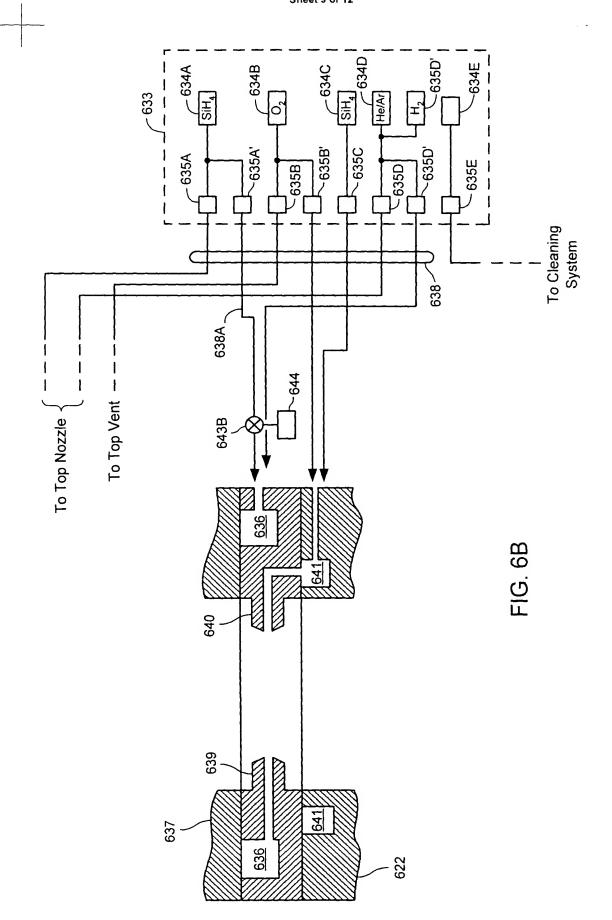
Statistics Data:

488Å Mean: 46.3Å StdD: 9.487 20.677 7.StdD: 7.NonU: 561Å Max: 359Å Min: Range: 8.1A Interval: 1.6547 Zinterval:

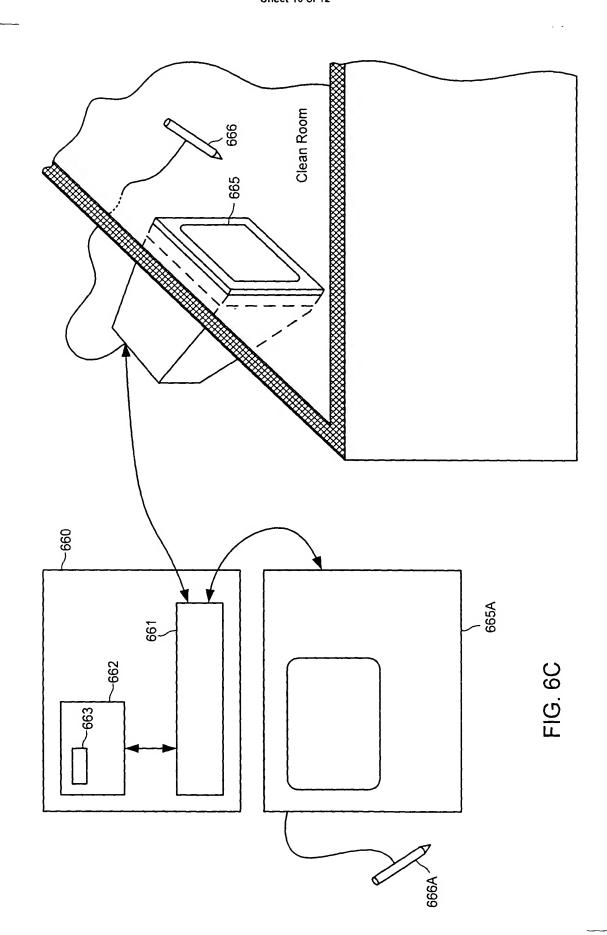
Comment: #7

Fig. 5E





Atty. Docket No.: A8067/T51700
Applicant: Hemant P. Mungekar et al.
Title: REACTIVE ION ETCHING FOR SEMICONDUCTOR DEVICE
FEATURE TOPOGRAPHY MODIFICATION
Sheet 10 of 12



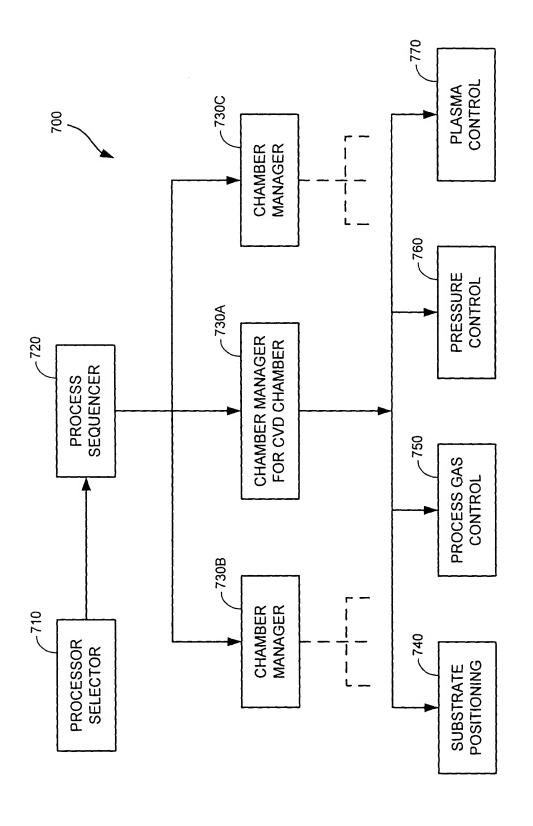


FIG. 6D

